CLC502 Clamping, Low-Gain Op Amp with Fast 14-bit Settling

General Description

The CLC502 is an operational amplifier designed for low-gain applications requiring output voltage clamping. This feature allows the designer to set maximum positive and negative output voltage levels for the amplifier – thus allowing the CLC502 to protect downstream circuitry, such as delicate converter systems, from destructive transients or signals which would otherwise cause saturation. The overload recovery time of only 8ns permits systems to resume operation quickly after overdrive.

High-accuracy systems will also benefit from the CLC502's fast, accurate settling. Settling to 0.0025% in 25ns (32ns guaranteed over temperature), the CLC502 is ideal as the input amplifier in high-accuracy (12 bits and above) A/D systems. Unlike most other high-speed op amps, the CLC502 is free of settling tails. And, as the settling plots show, settling to 0.01% accuracy is an even faster 18ns typical.

The CLC502 is also useful in other applications which require lowgain amplification (± 1 to ± 8) and the clamping or overload recovery features. For example, even low-resolution imaging circuits, which often have to cope with overloading signal levels, can benefit from clamping and overload recovery.

The CLC502 is available in several versions to meet a variety of requirements. A three-letter suffix determines the version:

CLC502AJP	-40°C to +85°C	8-pin plastic DIP
CLC502AJE	-40°C to +85°C	8-pin plastic SOIC

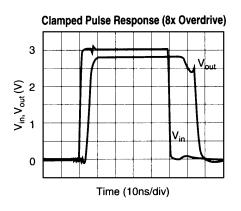
DESC SMD number: 5962-91743

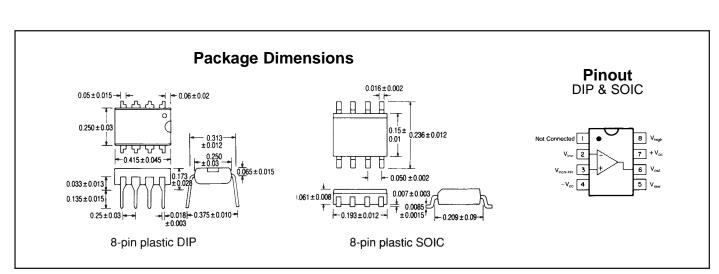
Features

- Output clamping with fast recovery
- 0.0025% settling in 25ns (32ns max.)
- Low power, 170mW
- Low distortion. -50dBc at 20MHz

Applications

- Output clamping applications
- High-accuracy A/D systems (12-14 bits)
- High-accuracy D/A converters
- Pulse amplitude modulation systems





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FREQUENCY DOMAIN PERFORMANCE 150 >100 >110 >100 MHz SSB 3dB bandwidth $V_{ant} < 0.5V_{pp}$ 150 >100 >110 >100 MHz SSB gain flatness $V_{ant} < 0.5V_{pp}$ 0 <0.4 <0.3 <0.4 dB GFPI peaking >25MHz 0 <0.7 <0.5 <0.7 dB GFPI Pictor dB GFPI Pictor dB GFPI Pictor dB GFPI Pictor <0 <0.7 <0.5 <0.7 dB GFPI Pictor dB GFPI Pictor <0 <0.7 <0.5 <0.7 dB GFPI Pictor dB CID <0.0 <1.0 <1.0 <1.0 <0.7 CID <0.7 CID SID SB SID SB SID SS SID SS SID SS SID SS SID SS SID SS SID SID SID SID <td< th=""><th>PARAMETER</th><th>CONDITIONS</th><th>TYP</th><th>MAX</th><th>& MIN RAT</th><th>INGS</th><th>UNITS</th><th>SYMBOL</th></td<>	PARAMETER	CONDITIONS	TYP	MAX	& MIN RAT	INGS	UNITS	SYMBOL
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		nolood				1	11	
output current $ \pm 55 > \pm 25 > \pm 45 > \pm 45 mA IO$		noioad						

Min/max ratings are based on product characterization and simulation. Individual parameters are tested as noted. Outgoing quality levels are determined from tested parameters.

Absolute Maximum	Ratings		Ν	iscellaneous Ratings
V _{cc} ± 7		recommen	ded ga	in range: ± 1 to ± 8
 lout output is short circuit protected to ground, but maximum reliability will be maintained if lout does not exceed common mode input voltage junction temperature operating temperature range AJ: storage temperature range lead solder duration (+ 300°C) ESD (human body model) 	70mA ± V∞ + 175°C - 40°C to + 85°C - 65°C to + 150°C 10 sec 1000V	NOTES: * note 1:	AJ	100% tested at + 25°C. Differential gain and phase measured at $A_v = +2V$, R = 250 Ω . R _L = 150 Ω , 1V _{pp} equivalent video signal, 0-100 IRE, 40 IRE _{pp} , 0 IRE = 0 volts, at 75 Ω load and 3.58 MHz.

Typical Performance Characteristics (T_A = 25°, A_V = +2, V_{CC} = ±5V, R_L = 100 Ω , R_f = 250 Ω , V_H = +3V, V_L = -3V)

 $A_v = -1$ $R_f = 249\Omega$

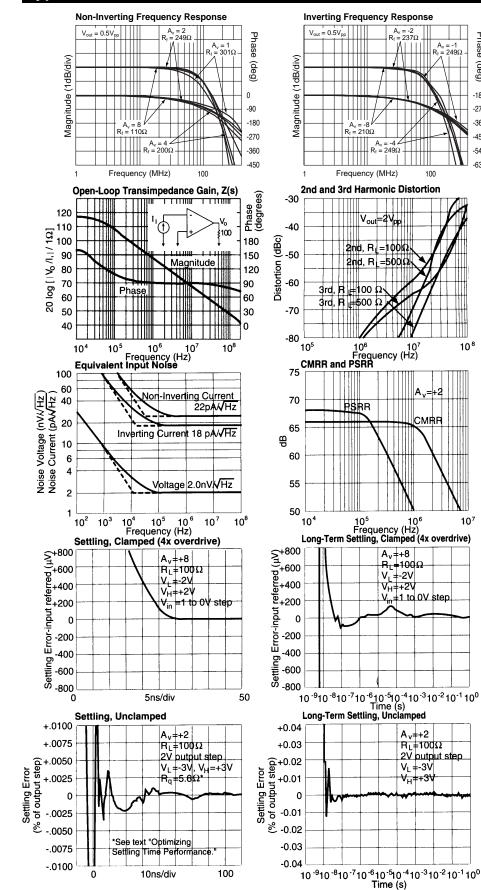
100

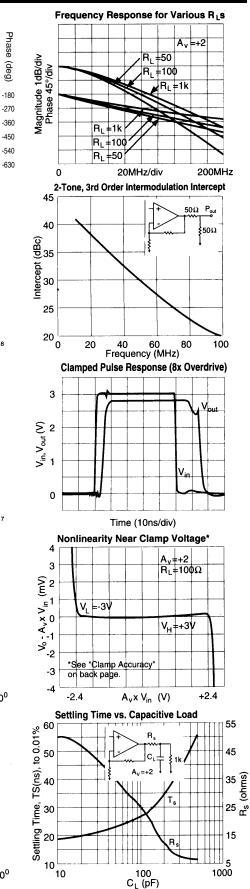
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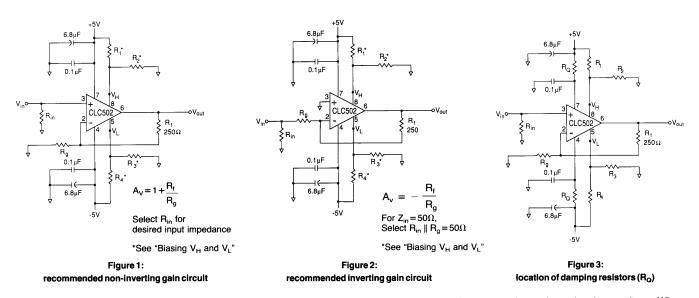
+31

10⁸

107







Clamp Operation

The maximum positive or negative excursion of the output voltage is determined by voltages applied to the clamping pins, V_H and V_L . V_H determines the positive clamping level; V_L determines the negative level. For example, if V_H is set at +2V and V_L is set at -0.5V the output voltage is restricted within this -0.5V to +2V range. When the output voltage tries to exceed this level, the amplifier goes into "clamp mode" and the output voltage limits at the clamp voltage.

Clamp Accuracy and Amplifier Linearity

Ideally, the clamped output voltage and the clamp voltage should be identical. In practice, however, there are two sources of clamp inaccuracy: the inherent clamp accuracy (which is shown in the specification page) and resistor divider action of open-loop output resistance of 10Ω and the load resistor. Or, in equation form,

$$V_{\text{out, clamp}} = (V_{\text{H or L}} \pm 300 \text{mV}) \frac{\text{R}_{\text{L}}}{\text{R}_{\text{L}} + 10\Omega}$$

When setting the clamp voltages, the designer should also recognize that within about 200mV of the clamp voltage, amplifier linearity begins to deteriorate. (See plot on previous page.)

Biasing V_H and V_L

Each of the clamping pins is buffered internally so simple resistive voltage divider circuits work well in providing the clamp voltages. V_L and V_H can be set by choosing the divider resistors using:

$$V_{H} = (5V) \left(\frac{R_2}{R_1 + R_2} \right)$$
 $V_{L} = (-5V) \left(\frac{R_3}{R_3 + R_4} \right)$

As a general guideline, let $R_1 + R_2 \cong R_3 + R_4 \cong 5k\Omega$.

 V_H should be biased more positively than V_L . V_H may be biased below 0V; however, with this biasing, the output voltage will actually clamp at 0V unless a simple pull down circuit is added to the op amp output (when clamped against V_H , the output cannot sink current). An analogous situation and design solution exists for V_L when it is biased above 0V, but in this case, a pull up circuit is used to *source* current when the amplifier is clamped against V_I .

The clamp voltage range rating is that for normal operation. Problems in overdriven linearity may occur if the clamps are set outside this range so this is not suggested under any conditions. If the clamping capability is not required, the CLC402 (low-gain op amp with fast 14-bit settling) may be the more appropriate part.

The clamps, which have a bandwidth of about 50MHz, may be driven by a high-frequency signal source. This allows the clamping level to be modulated, which is useful in many applications such as pulse amplitude modulation. The source resistance of the signal source should be less than 500 Ω to ensure stability.

Clamp-Mode Dynamics

As can be seen in the clamped pulse response plot on the previous page, clamping is virtually instantaneous. Note, however, that there can be a small amount of overshoot, as indicated on the specification page. The output voltage stays at the clamp voltage level as long as the product of the input voltage and the gain setting exceeds the clamp voltage. When the input voltage decreases, it will eventually reach a point where it is no longer trying to drive the output voltage above the clamp voltage. When this occurs, there is typically a 5-10ns "overload recovery from clamp," which is the time it takes for the op amp to resume linear operation. The normal op amp parameters, such as the rise time, apply when the op amp is in linear operation.

Optimizing Settling Time Performance

To obtain the best possible settling time performance for the CLC502, some additional design criteria must be considered, particularly when driving loads of less than 500 Ω . When driving a 100 Ω load, a step of a few volts on the output will create a large step of current in the power supplies. In some cases, this step will cause a small ringing on the power supply due to the bypass capacitor (.1 μ F) oscillating with the inductance in the power supply trace. The critical trace is the power supply trace between the two capacitors (a trace inductance of 20nH will be enough to degrade settling time performance). The frequency of the ring can be determined by

$$f = \frac{1}{2\pi \sqrt{C \cdot L_{Trace}}}$$

and any reduction in this frequency will improve performance due to better power supply rejection at lower frequencies. To obtain the best performance, a small resistor, R_Q, may be added in the trace to dampen the circuit (See Figure 3). An R_Q of 5-10 Ω will result in excellent settling performance and will have only minor impact on other performance characteristics. No provision for R_Q has been made on the evaluation board available from Comlinear as part #730013. It can, however, be easily added by cutting a trace and adding a 5-10 Ω resistor, as shown in Figure 3, for both supplies.

DC Accuracy and Noise

Since the two inputs for the CLC502 are quite dissimilar, the noise and offset error performance differs somewhat from that of a standard differential input amplifier. The two input bias currents are physically unrelated rendering bias current cancellation through matching of the inverting and non-inverting source resistance ineffective.

In Equation 3, the output offset is the algebraic sum of the equivalent input voltage and current sources that influence DC operation. Output noise is determined similarly except that a root-sum-of-squares replaces the algebraic sum. R_s is the non-inverting pin source resistance.

utput Offset
$$V_O = \pm IBN \times R_S(1 + R_f/R_g) \pm VIO (1 + R_f/R_g) \pm IBI \times R_f$$
 Eq. (3)

Printed Circuit Layout

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As with any high frequency device, a good PCB layout will enhance performance. Ground plane construction and good power supply bypassing close to the package are critical to achieving full performance. In the non-inverting configuration, the amplifier is sensitive to stray capacitance to ground at the inverting input. Hence, the inverting node connections should be small with minimal coupling to the ground plane. Shunt capacitance across the feedback resistor should not be used to compensate for this effect.

The device is also very sensitive to parasitic capacitance on the output pin. The plots include a suggested series R_s to de-couple this effect. Evaluation boards (part number 730013 for through-hole and 730027 for SOIC) for the CLC502 are available.

Package Thermal Resistance				
Package	οι ^θ	θ_{JA}		
AJP	65°C/W	120°C/W		
AJE	60°C/W	140°C/W		

Reliability Information

Transistor Count

Customer Design Applications Support

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